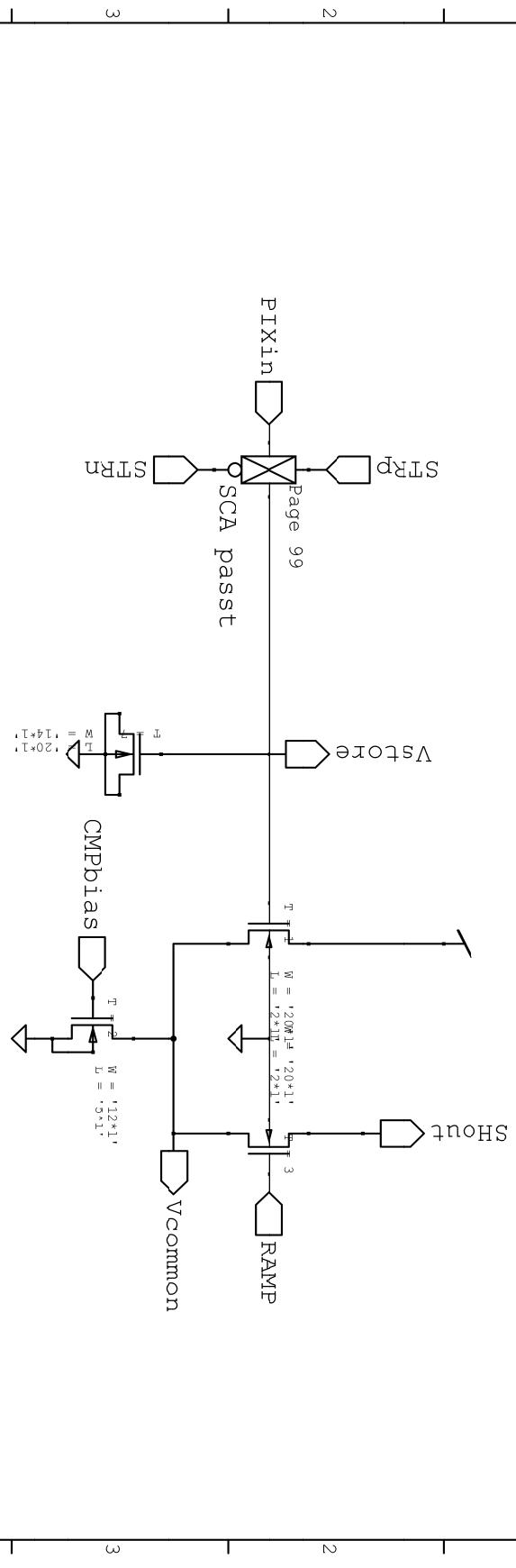


IRS Storage Base Cell (IRS_store_cell)



$$\text{Capacitance} = 201 * 141 \sim 4.032 \text{ um}^2 * \sim 4.8 \text{ fF/um}^2 = \sim 20 \text{ fF}$$

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```

<< Devices and Process Parameters >>
.param l=0.12A
1: the layout unit / scale factor (um).
P_4 / N_4: P / N-channel MOSFET
W: Gate width (1).
L: Gate Length (1).
AS / AD: Source/Drain Area A=W*L1*1 (1)
A: Area (sum) (1)
PS / PD: Source/Drain parameter P=(W*L1)*2*1 (1)
P: parameter (um). (1)
For SPICE Export, this .param statement must
be placed on top level of the design hierarchy.

```

[include models]

A B C D E F G